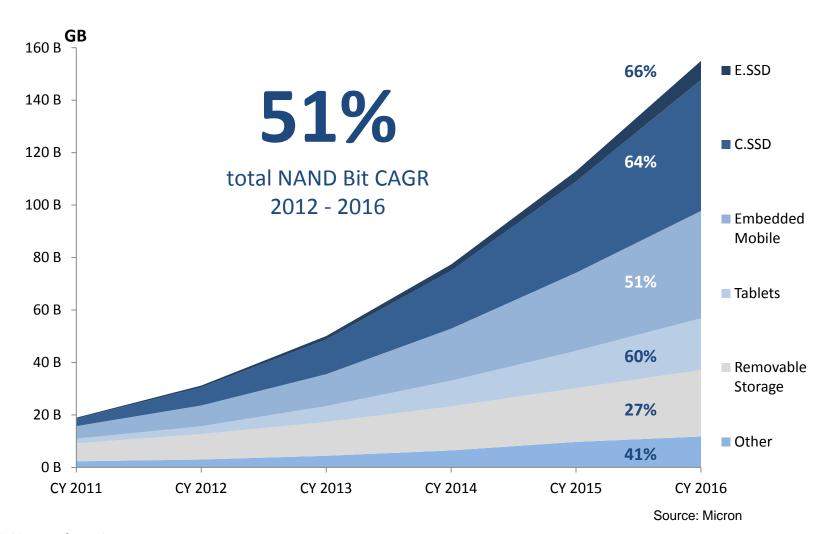


Need for Differentiated Endurance Solutions

Ji Luo
Micron Technology
NSG Product Marketing Manager

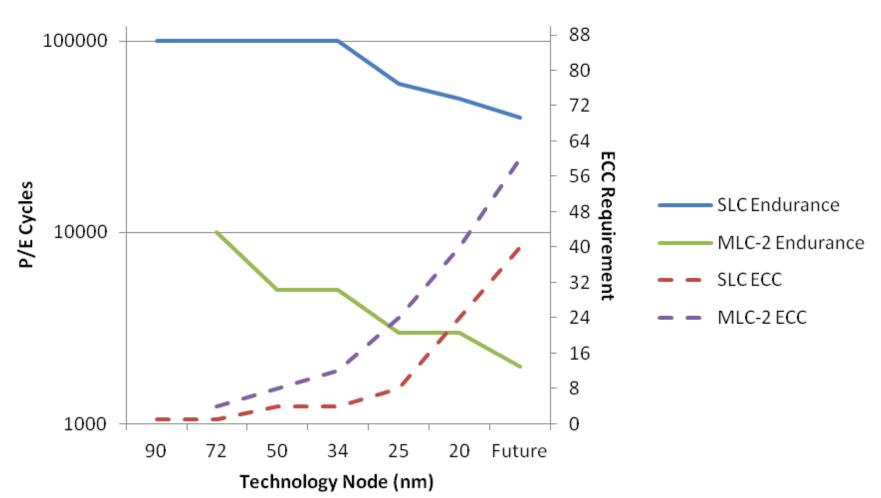


Memory NAND GB Growth By Segment





Current Endurance Trends vs. ECC



Source: Micron



Typical Density and Endurance Requirements / Segment

Application	2012 Mainstream MLC Product Density	Usage Model	Minimum Component P/E Cycle Expectation
Enterprise SSD	128-256GB	Mix Mode to Write Intensive	5K
Client SSD	64-128GB	Mix Mode	3K
Embedded Mobile	16GB	Read Intensive	3K
Tablets	4-8GB	Read Intensive	1.5K
Removable Storage	8-16GB	Read Intensive	500 Cycle



Key Careabouts Based on Usage



Read Intensive

- Fast data access
- Constrained by bus interface
- Read disturb for data integrity
- Low Latency



Mix Mode

- Needs based on usage model
- SLC partition to store code or cache data
- Low Latency



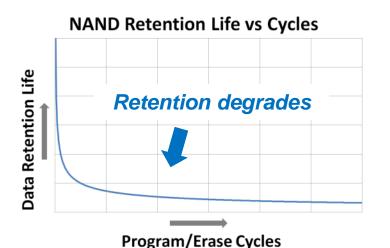
Write intensive

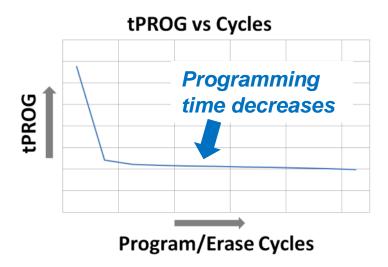
- Program and Erase Disturb
- Error management
- High Endurance important

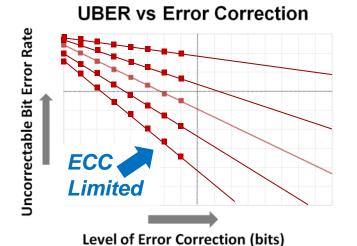
Flash Usage



Cycling Effects on Retention, tPROG, and ECC







Component tuning is required to maximize endurance



Ways to Tune Endurance



Component

- Reducing Retention
- Increasing Dwell Time
- Lowering Temperature
- Slowing Down Performance
- Increasing ECC



Controller

- Enhanced ECC and DSP
- Increase overprovisioning
- Reducing write amplification
- Increasing density



- Litho shrinks making endurance worse
- System level controls needed to maintain application endurance expectations
 - STEC Cellcare Technology*
 - Annobit Memory Signal Processing*
 - Micron RAIN Technology
 - LSI/Sandforce RAISE Technology*
- Tighter integration between NAND vendors and system controller critical in driving NAND adoption in the future